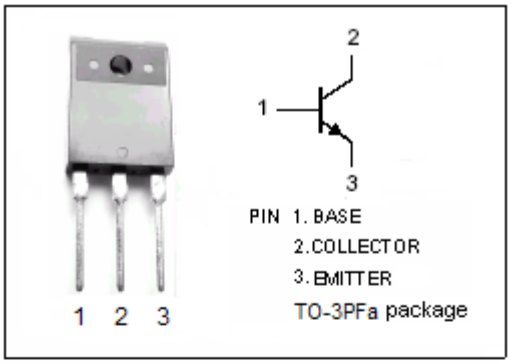
isc Silicon NPN Power Transistor 2SD1576

DESCRIPTION

- High Collector-Base Breakdown Voltage-
  : $V_{(BR)CBO}$= 1500V (Min.)
- High Switching Speed
- Wide Area of Safe Operation

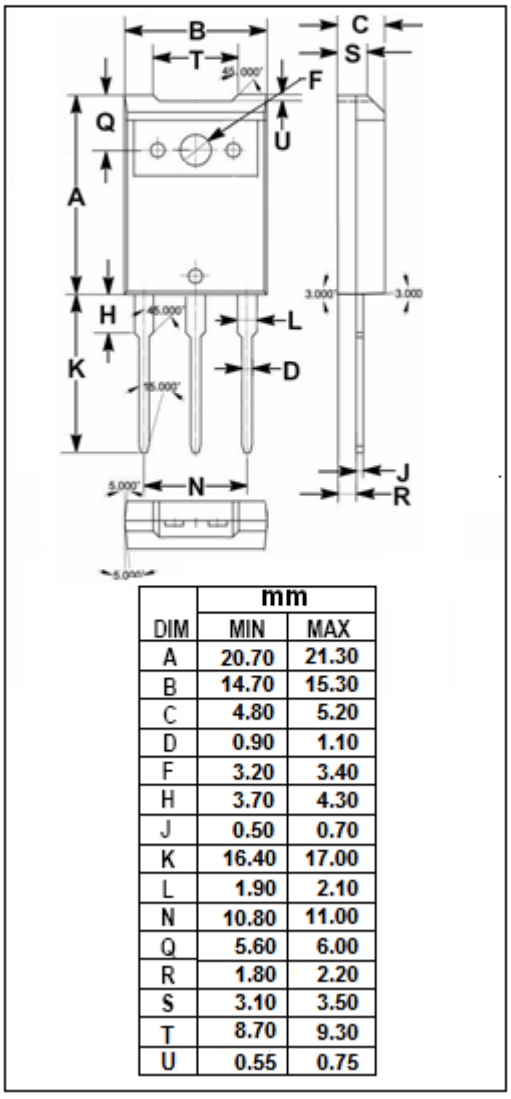


APPLICATIONS

- Designed for horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CES}	Collector- Emitter Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	700	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	2	A
I_{CM}	Collector Current-Peak	6	A
I_{BM}	Base Current-Peak	2.5	A
P_C	Collector Power Dissipation @ T_a=25℃	2.5	W
	Collector Power Dissipation @ T_C=25℃	80	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	20.70	21.30
B	14.70	15.30
C	4.80	5.20
D	0.90	1.10
F	3.20	3.40
H	3.70	4.30
J	0.50	0.70
K	16.40	17.00
L	1.90	2.10
N	10.80	11.00
Q	5.60	6.00
R	1.80	2.20
S	3.10	3.50
T	8.70	9.30
U	0.55	0.75

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B= 1A			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 2A; I_B= 1A			1.5	V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	6			V
I_{CBO}	Collector Cutoff Current	V_{CB}= 750V; I_E= 0 V_{CB}= 1500V; I_E= 0			50 1.0	μA mA
h_{FE}	DC Current Gain	I_C= 2A; V_{CE}= 5V	2			
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 10V; f_{test}= 0.5MHz		2		MHz

Switching times

t_{stg}	Storage Time	I_C= 2.5A , I_B= 1.1A; L_B= 10μH			9.0	μs
t_f	Fall Time				1.0	μs